

## 100V N-Channel Power MOSFET

### DESCRIPTION :

- Excellent  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $\Delta V_{DS}$  Tested
- Pb-Free Lead Plating
- RoHS compliant
- Halogen Free

$V_{DS}$	100V
$I_D (T_C=25^\circ C)$	120A
$R_{DS(ON)_Typ. @ V_{GS}=10V}$	11.6m $\Omega$

### TYPICAL APPLICATIONS :

- Power Management
- Load Switch
- PWM Application



TO-247-3L

### MAXIMUM RATINGS (at $T_C = 25^\circ C$ , unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current		$I_D$	120	A
Single Pulsed Avalanche Energy <sup>(1)</sup>		$E_{AS}$	144	mJ
Junction & Storage temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

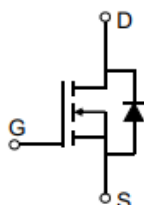
Notes : 1. EAS condition: Starting  $T_J=25^\circ C$ ,  $V_{DD}=50V$ ,  $V_{GS}=10V$ ,  $R_G=25\Omega$ ,  $L=0.5mH$ ,  $I_{AS}=24A$ ,  $V_{DD}=0V$  during time in avalanche.

### ELECTRICAL CHARACTERISTICS (at $T_J = 25^\circ C$ , unless otherwise specified)

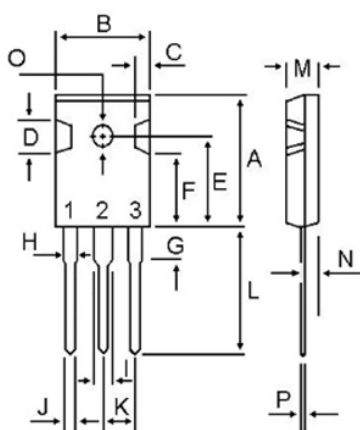
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0V, I_D = 250\mu A$	$V_{(BR)DSS}$	100			V
Zero Gate Voltage Drain Current $V_{DS} = 100V, V_{GS} = 0V$	$I_{DSS}$			1	$\mu A$
Gate-Source Leakage Current $V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$			$\pm 100$	nA

Gate-Source threshold voltage V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	V <sub>GS(th)</sub>	2.0	3.0	4.0	V
Drain-Source On-State Resistance V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A V <sub>GS</sub> = 8V, I <sub>D</sub> = 30A	R <sub>DS(on)</sub>		11.6 12.2	15.0 16.0	mΩ
Input capacitance f=1MHz, V <sub>DS</sub> =50 V, V <sub>GS</sub> =0 V	C <sub>iss</sub>		4930		pF
Output capacitance f=1MHz, V <sub>DS</sub> =50 V, V <sub>GS</sub> =0 V	C <sub>oss</sub>		180		pF
Reverse transfer capacitance f=1MHz, V <sub>DS</sub> =50 V, V <sub>GS</sub> =0 V	C <sub>rss</sub>		168		pF
Gate Resistance f=1MHz, V <sub>DS</sub> =0 V, V <sub>GS</sub> =0 V	R <sub>g</sub>		0.7		Ω

• Circuit diagram



• TO-247-3L Package outlines : Dimensions in (mm)



DIM	MILLIMETERS	
	MIN	MAX
A	20.80	21.80
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.50	15.50
F	11.20	13.20
G	3.75	4.35
H	1.90	2.30
I	2.90	3.30
J	1.00	1.40
K	5.26	5.66
L	19.50	20.50
M	4.68	5.36
N	2.30	2.60
O	3.45	3.85
P	0.48	0.72

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